

Substitute Abstract of the Disclosure

A method for manufacturing a semiconductor device having a substrate as a workpiece in which an insulation film is formed onto the substrate, openings are formed in the insulation film, a first conductive film is formed inside the openings and on a surface of the insulation film, a second conductive film is formed on the first conductive film, by planarizing the second conductive film and part of the first conductive film, rising a fixed abrasive tool, and the first and the second planarized conductive films are formed in the openings, by planarizing a surface of the second conductive film and a surface of part of the first conductive film using a fixed abrasive tool. The method involve supplying a first processing liquid comprising about 30% oxidizing agent upon planarization of the second conductive film and planarizing the surface of the second conductive film with the first processing liquid and the fixed abrasive tool, switching the liquid supply from first processing liquid to a second processing liquid including about 5% oxidizing agent upon planarization of the second and the first conductive film and planarizing the surface of the second conductive film and the surface of the part of the first conductive film with the second processing liquid and the fixed abrasive tool, thereby a plurality of planarizing steps are constituted in a single planarizing step.